

Title (en)

OPTOELECTRONIC DEVICE AND METHOD FOR MANUFACTURING SAME

Title (de)

OPTOELEKTRONISCHE VORRICHTUNG UND VERFAHREN ZUR HERSTELLUNG DAVON

Title (fr)

DISPOSITIF OPTOÉLECTRONIQUE ET PROCÉDÉ DE FABRICATION

Publication

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Application

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Abstract (en)

[origin: WO2023274828A1] The invention relates to a transfer structure (501, 502, 503) comprising a substrate (401, 402, 403) and an optoelectronic device (301, 302, 303) attached to the substrate, the substrate comprising a base portion (42) having a substrate face (400), and at least one element (41) projecting from the substrate face (400), the optoelectronic device having a first face (301) comprising a central zone (301c) and a peripheral zone (301p) surrounding the central zone, the transfer structure being characterised in that the at least one projecting element (41) of the substrate is attached to the peripheral zone (301p) of the first face of the optoelectronic device. The invention also relates to a method for transferring optoelectronic devices, which method is based on the implementation of transfer structures.

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